

Electrical Characteristics

at $T_j = 25\text{ °C}$, unless otherwise specified.

Parameter	Symbol	Values			Unit
		min.	typ.	max.	

Static Characteristics

Drain-source breakdown voltage $V_{GS} = 0, I_D = 0.25\text{ mA}$	$V_{(BR)DSS}$	100	–	–	V
Gate threshold voltage $V_{GS} = V_{DS}, I_D = 1\text{ mA}$	$V_{GS(th)}$	1.5	2.0	2.5	
Zero gate voltage drain current $V_{GS} = 0\text{ V}, V_{DS} = 100$ $T_j = 25\text{ °C}$ $T_j = 125\text{ °C}$	I_{DSS}	– –	0.1 10	1.0 100	μA
Gate-source leakage current $V_{GS} = \pm 20\text{ V}, V_{DS} = 0$ $T_j = 25\text{ °C}$ $T_j = 150\text{ °C}$	I_{GSS}	– –	10 2	100 4	nA μA
Drain-source on-state resistance $V_{GS} = 4.5\text{ V}, I_D = 9.5\text{ A}$	$R_{DS(on)}$	–	0.085	0.1	Ω

Dynamic Characteristics

Forward transconductance $V_{DS} \geq 2 \times I_D \times R_{DS(on)max}, I_D = 9.5\text{ A}$	g_{fs}	8	14	–	S
Input capacitance $V_{GS} = 0, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$	C_{iss}	–	1200	1500	pF
Output capacitance $V_{GS} = 0, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$	C_{oss}	–	320	580	
Reverse transfer capacitance $V_{GS} = 0, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$	C_{rss}	–	160	260	
Turn-on time $t_{on}, (t_{on} = t_{d(on)} + t_r)$ $V_{CC} = 30\text{ V}, V_{GS} = 5\text{ V}, I_D = 3\text{ A}, R_{GS} = 50\text{ Ω}$	$t_{d(on)}$	–	25	40	ns
	t_r	–	110	170	
Turn-off time $t_{off}, (t_{off} = t_{d(off)} + t_f)$ $V_{CC} = 30\text{ V}, V_{GS} = 5\text{ V}, I_D = 3\text{ A}, R_{GS} = 50\text{ Ω}$	$t_{d(off)}$	–	210	270	
	t_f	–	100	130	

Electrical Characteristics (cont'd)

 at $T_j = 25\text{ °CC}$, unless otherwise specified.

Parameter	Symbol	Values			Unit
		min.	typ.	max.	

Reverse Diode

Continuous source current	I_S	–	–	19	A
Pulsed source current	I_{SM}	–	–	76	
Diode forward on-voltage $I_F = 22\text{ A}$, $V_{GS} = 0\text{ V}$	V_{SD}	–	1.2	1.5	V
Reverse recovery time $I_F = I_S$, $di_F/dt = 100\text{ A}/\mu\text{s}$, $V_R = 30\text{ V}$	t_{rr}	–	150	–	ns
Reverse recovery charge $I_F = I_S$, $di_F/dt = 100\text{ A}/\mu\text{s}$, $V_R = 30\text{ V}$	Q_{rr}	–	0.58	–	μC

Temperature Sensor

Forward voltage $I_{TS(on)} = 5\text{ mA}$, $T_j = -55 \dots +150\text{ °C}$ Sensor override, $t_p \leq 100\text{ }\mu\text{s}$ $T_j = -55 \dots +160\text{ °C}$	$V_{TS(on)}$	–	1.3	1.4	V
		–	–	10	
Forward current $T_j = -55 \dots +150\text{ °C}$ Sensor override, $t_p \leq 100\text{ }\mu\text{s}$ $T_j = -55 \dots +160\text{ °C}$	$I_{TS(on)}$	–	–	5.0	mA
		–	–	600	
Holding current, $V_{TS(off)} = 5\text{ V}$, $T_j = 25\text{ °C}$ $T_j = 150\text{ °C}$	I_H	0.05 0.05	0.1 0.2	0.5 0.3	
Switching temperature $V_{TS} = 5\text{ V}$	$T_{TS(on)}$	150	–	–	°C
Turn-off time $V_{TS} = 5\text{ V}$, $I_{TS(on)} = 2\text{ mA}$	t_{off}	0.5	–	2.5	μs

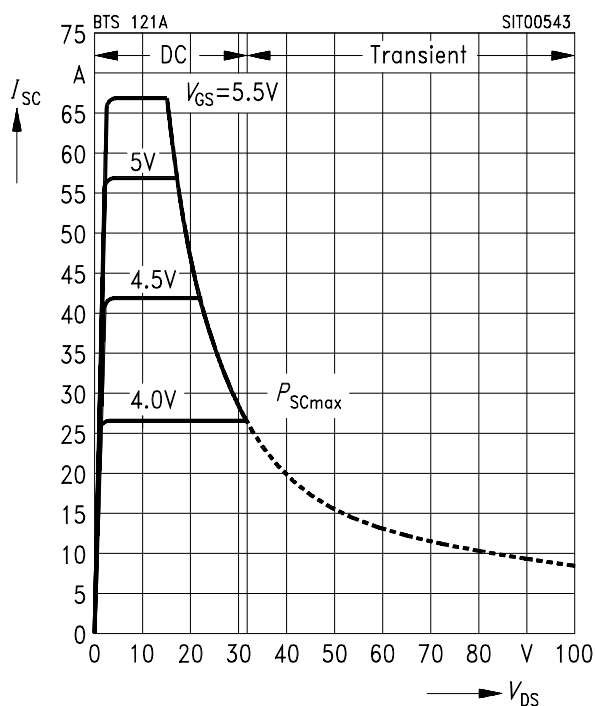
Examples for short-circuit protection

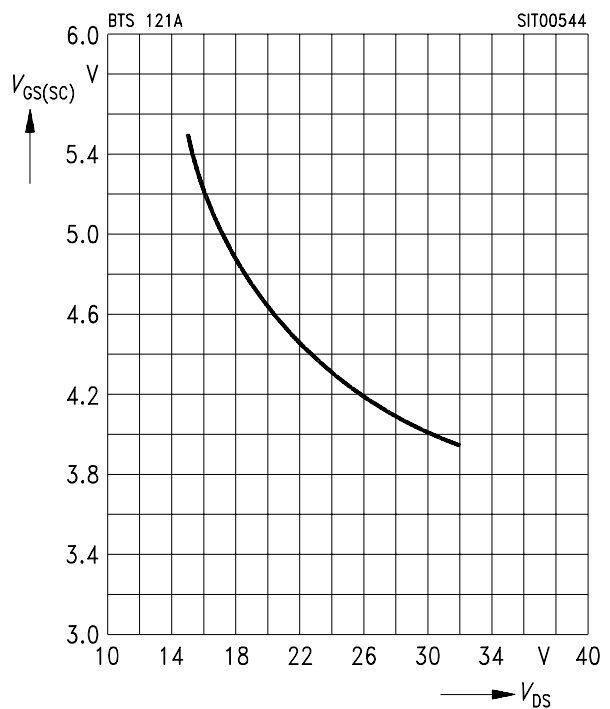
 at $T_j = -55 \dots +150 \text{ }^\circ\text{C}$, unless otherwise specified.

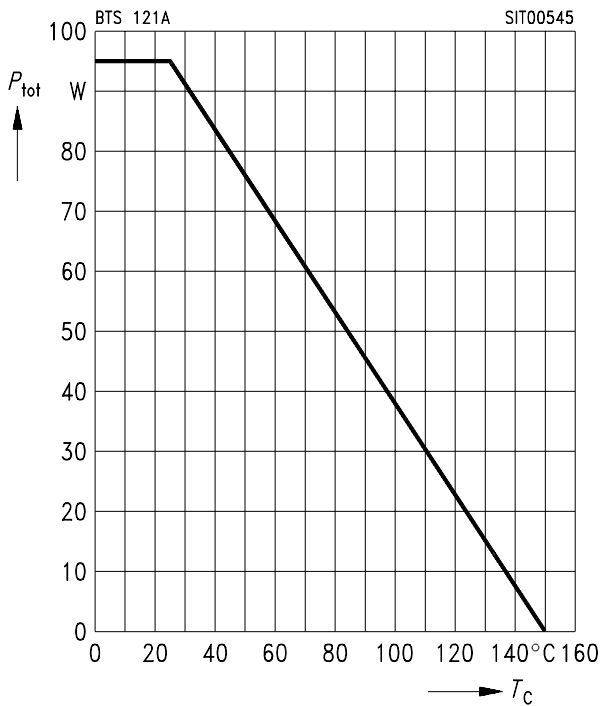
Parameter	Symbol	Examples			Unit
		1	2	–	
Drain-source voltage	V_{DS}	15	30	–	V
Gate-source voltage	V_{GS}	5.5	4.0	–	
Short-circuit current	I_{SC}	66.7	26.7	–	A
Short-circuit dissipation	P_{SC}	1000	800	–	W
Response time $T_j = 25 \text{ }^\circ\text{C}$, before short circuit	$t_{SC(off)}$	≤ 25	≤ 25	–	ms

Short-circuit protection $I_{SC} = f(V_{DS})$

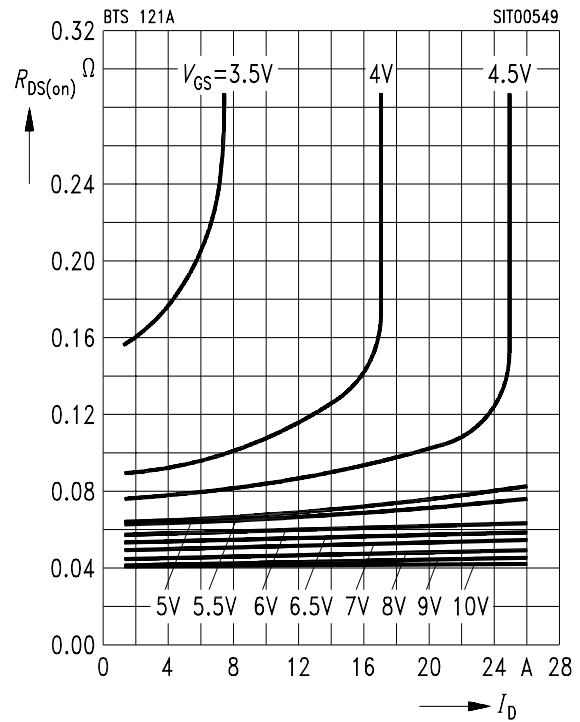
 Parameter: V_{GS}

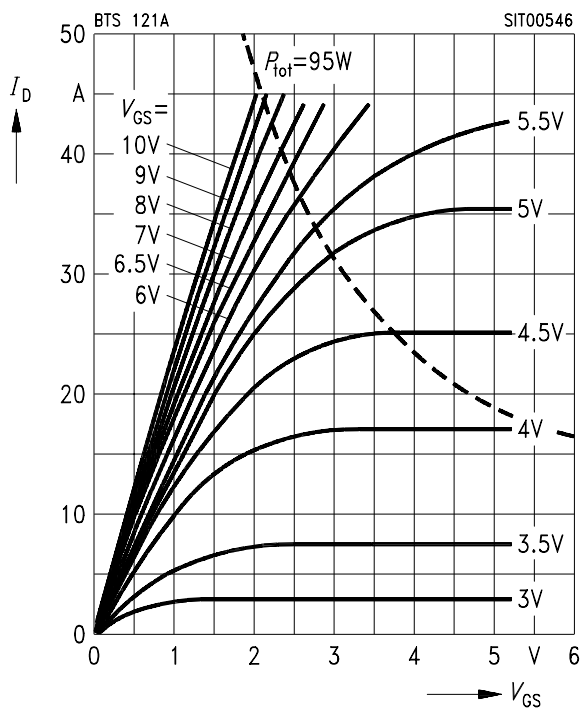
 Diagram to determine I_{SC} for $T_j = -55 \dots +150 \text{ }^\circ\text{C}$

Max. gate voltage $V_{GS(SC)} = f(V_{DS})$

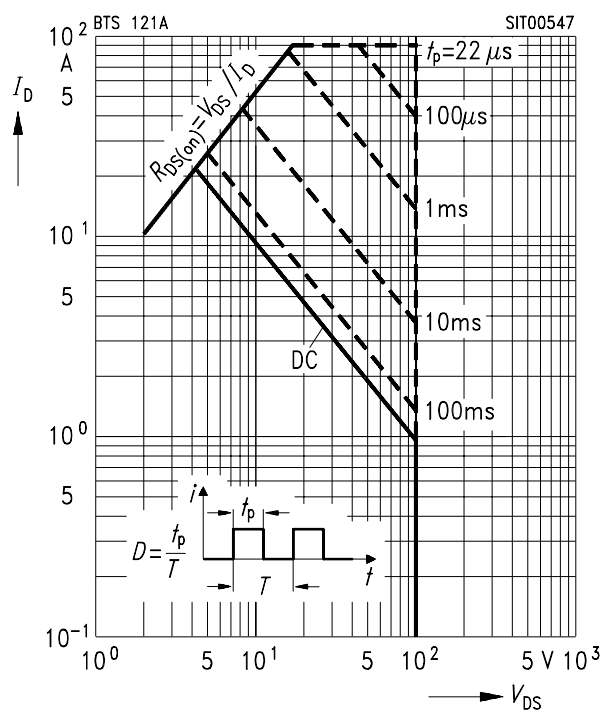
 Parameter: $T_j = -55 \dots +150 \text{ }^\circ\text{C}$


Max. power dissipation $P_{\text{tot}} = f(T_C)$

Typ. drain-source on-state resistance $R_{\text{DS(on)}} = f(I_D)$

$$R_{\text{DS(on)}} = f(I_D)$$

 Parameter: V_{GS}

Typical output characteristics $I_D = f(V_{\text{DS}})$

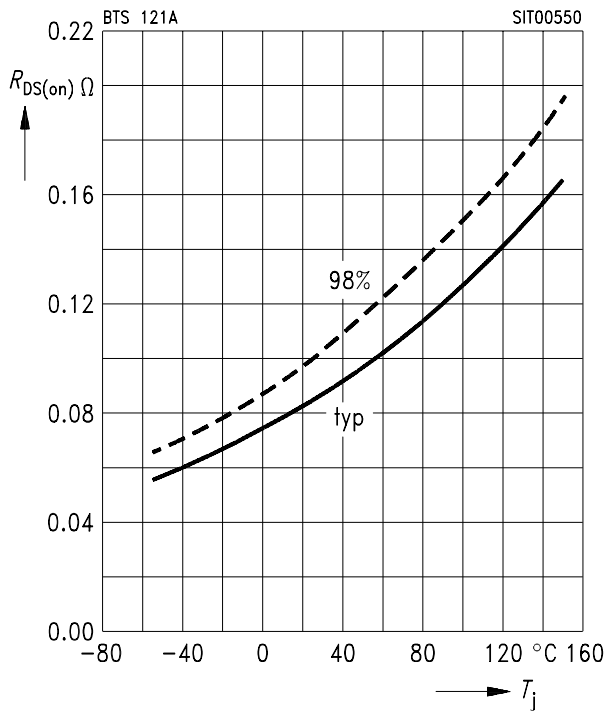
 Parameter: $t_p = 80 \mu\text{s}$

Safe operating area $I_D = f(V_{\text{DS}})$

 Parameter: $D = 0.01$, $T_C = 25^\circ\text{C}$


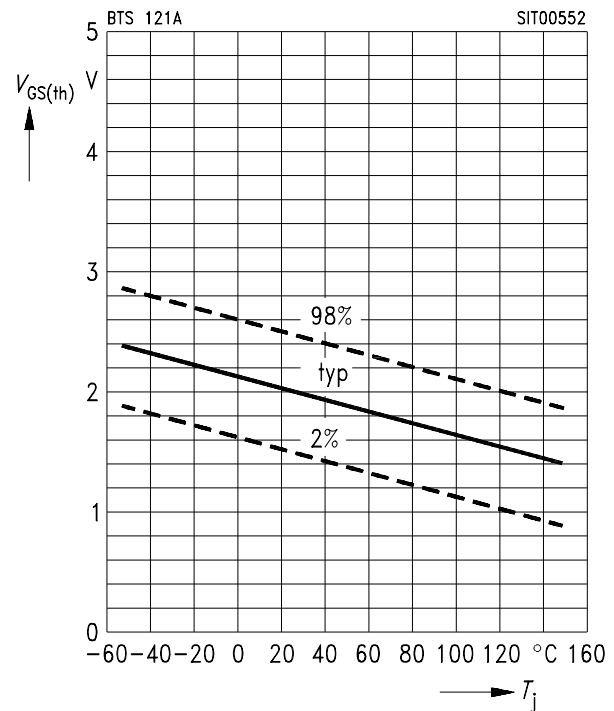
Drain-source on-state resistance

$$R_{DS(on)} = f(T_j)$$

Parameter: $I_D = 4.5 \text{ A}$, $V_{GS} = 9.5 \text{ V}$

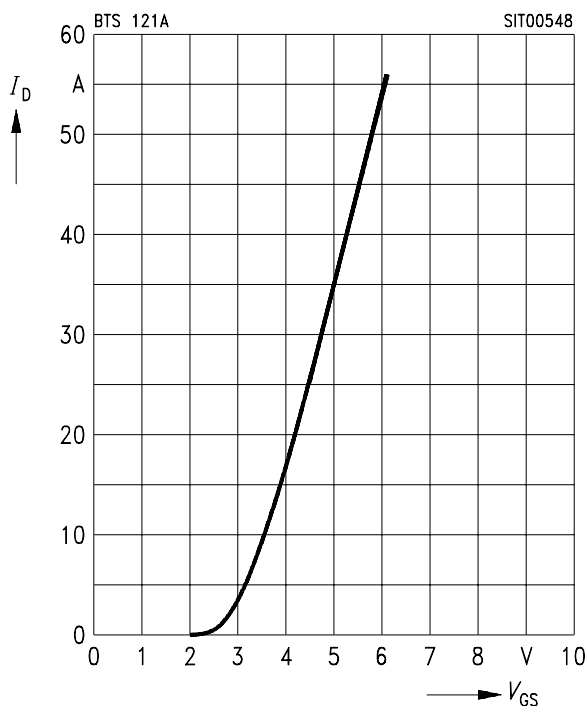

Gate threshold voltage $V_{GS(th)} = f(T_j)$

Parameter: $V_{DS} = V_{GS}$, $I_D = 1 \text{ mA}$ (spread)

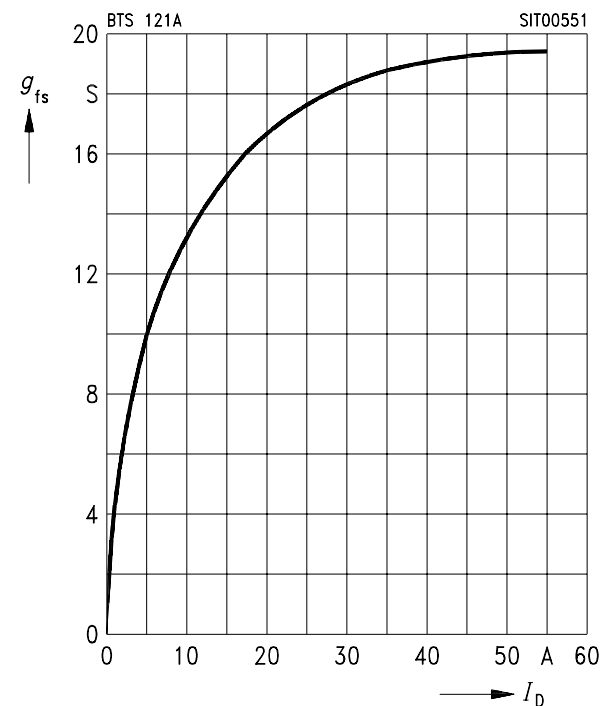

Typ. transfer characteristic

$$I_D = f(V_{GS})$$

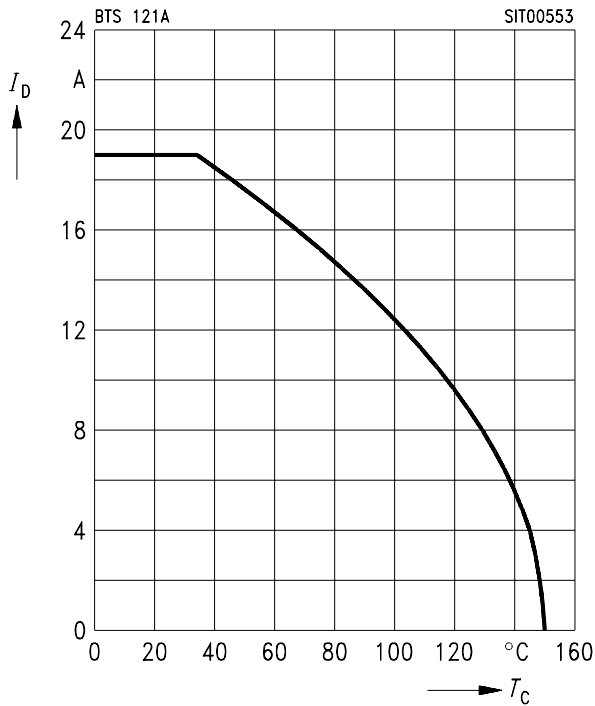
Parameter: $t_p = 80 \mu\text{s}$, $V_{DS} = 25 \text{ V}$

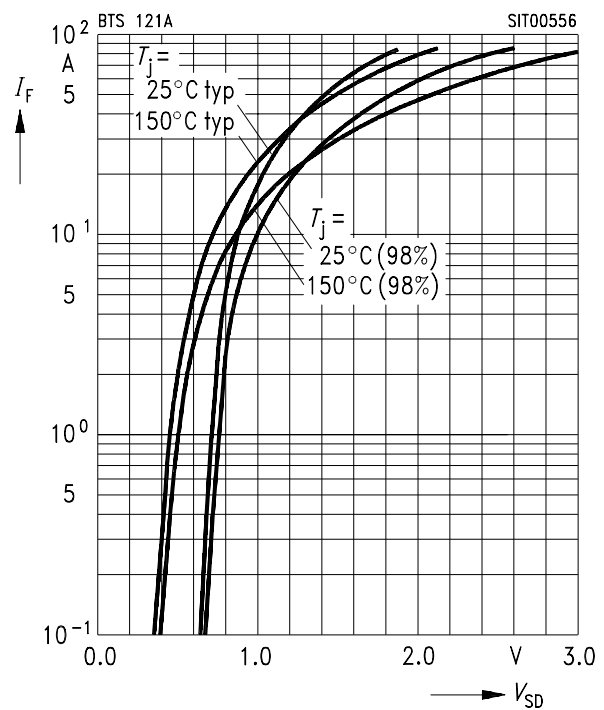

Typ. transconductance $g_{fs} = f(I_D)$

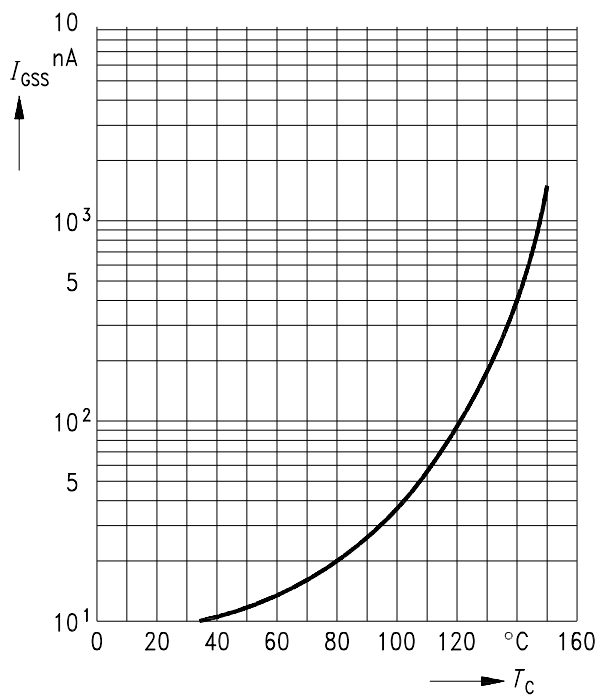
Parameter: $t_p = 80 \mu\text{s}$, $V_{DS} = 25 \text{ V}$

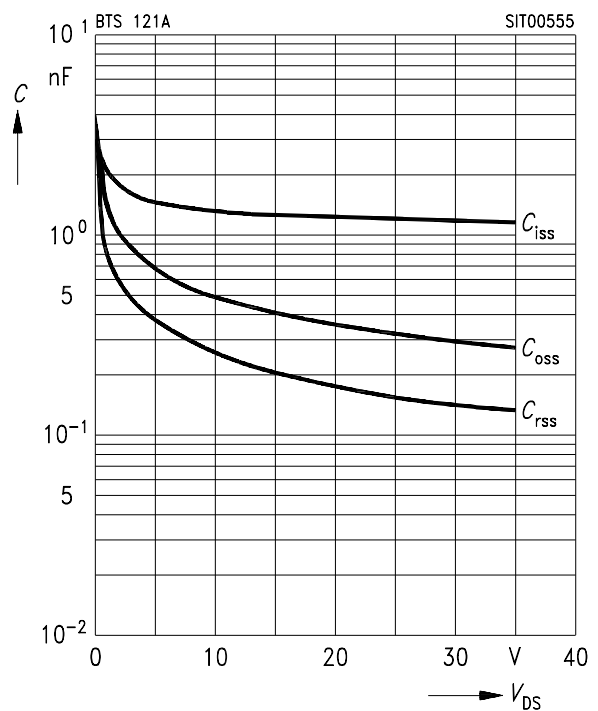


Continuous drain current $I_D = f(T_C)$

 Parameter: $V_{GS} \geq 10 \text{ V}$

Forward characteristics of reverse diode
 $I_F = f(V_{SD})$

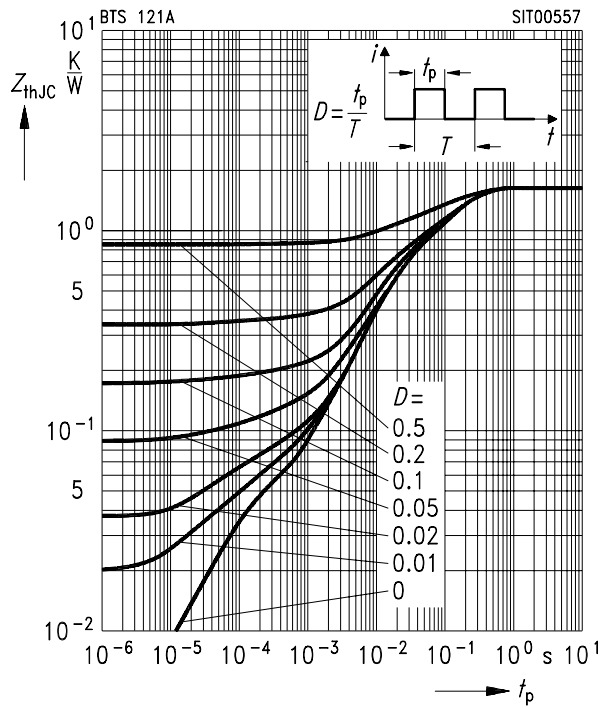
 Parameter: $T_j, t_p = 80 \mu\text{s}$ (spread)

Typ. gate-source leakage current
 $I_{GSS} = f(T_C)$

 Parameter: $V_{GS} = 20 \text{ V}, V_{DS} = 0$

Typ. capacitances $C = f(V_{DS})$

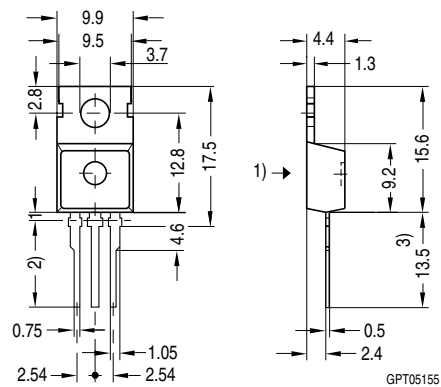
 Parameter: $V_{GS} = 0, f = 1 \text{ MHz}$


Transient thermal impedance $Z_{thJC} = f(t_p)$

Parameter: $D = t_p/T$

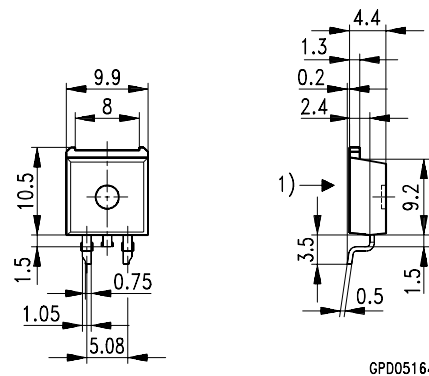


TO 220 AB
Standard

Ordering Code
C67078-S5010-A2


- 1) punch direction, burr max. 0.04
- 2) dip tinning
- 3) max. 14.5 by dip tinning press burr max. 0.05

TO 220 AB
SMD Version E 3045

Ordering Code
C67078-S5010-A5


- 1) shear and punch direction no burrs this surface

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